

# Precision Analog Microcontroller with RF Transceiver, ARM Cortex<sup>™</sup>-M3

**Preliminary Technical Data** 

# ADuCRF101

### **FEATURES**

Analog I/O 6-Channel 14-bit or 12-bit ADC Single ended and differential inputs Programmable data rate up to 842 kSPS **On-Chip Voltage Reference and Temperature Sensor** Power Supply Range: 2.2 V to 3.6 V **Power Consumption** 680 nA, in power down mode, non-retained state 1.6 µA, in power down mode, processor memory and transceiver memory retained 190 µA / MHz, Cortex in Active mode 12.8 mA transceiver in receive mode, Cortex in power down mode 9 mA to 32 mA transceiver in transmit mode, Cortex in power down mode **RF Transceiver Frequency bands** 862 MHz to 928 MHz 431 MHz to 464 MHz **Multiple Configurations supported Receiver sensitivity (BER)** -107.5 dBm at 38.4 kbps, 2FSK Single ended and differential PA Low External BOM Microcontroller ARM Cortex<sup>™</sup>-M3 32-bit processor Serial Wire download and debug

**External Watch crystal for wakeup timer** 16 MHz internal Oscillator with 8-way Programmable Divider Memory 128 k Bytes /64 k Bytes Flash/EE Memory, 16 k Bytes /8 k **Bytes SRAM** 20000 cycle Flash/EE endurance 10 year Flash/EE retention In-circuit download via Serial Wire and UART **On-Chip Peripherals** UART, I<sup>2</sup>C and SPI Serial I/O 28-Pin GPIO Port 2 General Purpose Timers Wake-up Timer Watchdog Timer 8-Channel PWM **Packages and Temperature Range** 64 lead LFCSP (9mm x 9mm) package -40°C to 85°C Tools Low-Cost Development System **Third-Party Compiler and emulator tool Support** 

#### **APPLICATIONS**

Battery powered wireless sensor Medical telemetry systems Industrial and home automation Asset tracking Security systems (access systems) Health and fitness applications

### FUNCTIONAL BLOCK DIAGRAM

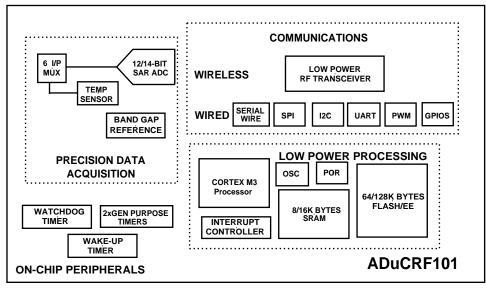


Figure 1. ADuCF101 Block Diagram

#### Rev. PrG

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective companies.

# TABLE OF CONTENTS

Features	1
Functional block diagram	1
General Description	3
Specifications	4
Absolute Maximum Ratings	9

ESD Caution	9
Pin Configuration and Function Descriptions	
Outline Dimensions	13
Ordering Guide	13

## **GENERAL DESCRIPTION**

The ADuCRF101 is a fully integrated data acquisition solution designed for low power wireless applications. It features a 12-bit or 14-bit ADC, a low power Cortex<sup>™</sup>-M3 processor from ARM<sup>\*</sup>, a 431 MHz to 464 MHz and 862 MHz to 928 MHz RF transceiver, and Flash/EE memory packaged in a 9 mm × 9 mm LFCSP.

The acquisition section consists of a 12-bit / 14-bit ADC SAR ADC. The six inputs can be configured as single ended or differential modes. When configured in single ended mode, they can be used for ratiometric measurements on sensors, powered when required from the internal LDO. An internal battery monitor channel and an on-chip temperature sensor are also available.

This wireless data acquisition system is designed to operate in battery-powered applications where low power is critical. The device can be configured in normal operating mode or different low power modes under direct program control. In flexi mode any peripheral can operate and wake-up the device. In hibernate mode the internal wake-up timer remains active. In shutdown mode only an external interrupt can wake-up the device.

The ADuCRF101 integrates a low power Cortex-M3 processor from ARM. It is a 32-bit RISC machine, offering up to 1.25 DMIPS peak performance. The Cortex-M3 processor also has a flexible 14-channel DMA controller supporting communication peripherals SPI, UART and I<sup>2</sup>C. 64 kB / 128 kB of nonvolatile Flash/EE memory and 8 kB / 16 kB of SRAM are also provided on-chip. A 16 MHz on-chip oscillator generates the system clock. This clock can be internally divided for the processor to operate at lower frequency for power saving reasons. A low power internal 32 kHz oscillator is available and can used to clock the timers. There are two general-purpose timers, a wake-up timer and a system watchdog timer.

A range of communication peripherals can be configured as required in a specific application. These peripherals include UART, I<sup>2</sup>C, SPI, GPIO ports, PWM and RF transceiver.

The RF transceiver communicates in the 431 MHz to 464 MHz and 862 MHz to 928 MHz frequency bands using multiple configurations.

On-chip factory firmware supports in-circuit serial download via the UART while nonintrusive emulation and program download is also supported via the serial wire interface. These features are incorporated into a low cost development system supporting this precision analog microcontroller family.

The parts operate from 2.2 V to 3.6 V and are specified over an industrial temperature range of  $-40^{\circ}$ C to  $+85^{\circ}$ C.

Three versions of the ADuCRF101 are available:

- 14-bit ADC, 128 k Byte Flash and 16 k Byte SRAM
- 12-bit ADC, 128 k Byte Flash and 16 k Byte SRAM
- 12-bit ADC, 64 k Byte Flash and 8 k Byte SRAM

### **SPECIFICATIONS**

### **ELECTRICAL SPECIFICATIONS**

 $AVDD = IOVDD = VDDBAT1 = VDDBAT2 = 2.2 V to 3.6 V, V_{REF} = 1.25 V internal reference, f_{CORE} = 16 MHz, T_A = -40^{\circ}C to +85^{\circ}C$  unless otherwise noted. Default ADC sampling frequency: eight acquisition clocks and ADC clock frequency of 4 MHz.

Table 1. 12	Bit ADC channel	specification

Parameter	Test Conditions / Comments	Min	Тур	Max	Unit
DC ACCURACY	Single ended input mode. Applies to all ADC input channels.				
Resolution			12		Bits
Integral Nonlinearity	$V_{REF} = 1.25 V$ from internal reference		±1		LSB
	$V_{REF} = 1.8 V$ from LDO		±2		LSB
Differential Nonlinearity	Guaranteed no missing code		±1		LSB
DC Code Distribution	ADC input is a DC voltage		2		LSB
CALIBRATED ENDPOINT ERRORS	Measured using the factory-set default values ADCOF and ADCGN.				
Offset Error			±0.6		LSB
Offset Error Match			±0.25		LSB
Gain Error			±1.25		LSB
Gain Error Match			±0.25		LSB
DYNAMIC PERFORMANCE	$f_{IN} = 10 \text{ kHz}$ sine wave.				
Signal-to-Noise Ratio (SNR)			68		dB
Total Harmonic Distortion			TBD		
Peak Harmonic or Spurious Noise (PHSN)			TBD		
Channel-to-Channel Crosstalk	Measured on adjacent channels		TBD		

#### Table 2. 14 Bit ADC channel specification

Parameter	Test Conditions/Comments	Min	Тур	Max	Unit
ADC SPECIFICATIONS					
DC ACCURACY	Single ended input mode. Applies to all ADC input channels.				
Resolution			14		Bits
Integral Nonlinearity	$V_{REF} = 1.25 V$ from internal reference		±4		LSB
	$V_{REF} = 1.8 V$ from LDO		±8		LSB
Differential Nonlinearity	Guaranteed no missing code		±1		LSB
DC Code Distribution	ADC input is a DC voltage		8		LSB
CALIBRATED ENDPOINT ERRORS	Measured using the factory-set default values ADCOF and ADCGN.				
Offset Error			±2.5		LSB
Offset Error Match			±1		LSB
Gain Error			±5		LSB
Gain Error Match			±1		LSB
DYNAMIC PERFORMANCE	$f_{IN} = 10 \text{ kHz}$ sine wave.				
Signal-to-Noise Ratio (SNR)			80		dB
Total Harmonic Distortion			TBD		
Peak Harmonic or Spurious Noise (PHSN)			TBD		
Channel-to-Channel Crosstalk	Measured on adjacent channels		TBD		

### Table 3. ADuCRF101 Specification

Parameter	Test Conditions/Comments	Min	Тур	Max	Unit
ADC SPECIFICATIONS					
ANALOG INPUT					
Input Voltage Ranges <sup>1</sup>					
Single ended input		0		VREF	V
Differential input		0		$V_{CM} \pm V_{REF}/2$	V
Leakage Current			100		nA
Input Capacitance	During ADC Acquisition		20		рF
ADC Power-up Time	Excludes reference power up time		5		μs
ON-CHIP VOLTAGE REFERENCE					
Output Voltage			1.25		V
Accuracy	Measured at $T_A = 25^{\circ}C$		±5		mV
Reference Temperature Co			±40		ppm/°C
Power Supply Rejection Ratio			60		dB
Output Impedance			2		Ω
Internal V <sub>REF</sub> Power-On Time	0.47µF external capacitor		5		ms
TEMPERATURE SENSOR <sup>1</sup>	Indicates die temperature		2		1115
Voltage Output at 25°C			TBD		mV
Voltage TC			TBD		mV/°C
-	MCI Lin low newsrands		TBD		°C
Accuracy Thormal impodance	MCU in low power mode				
			TBD		
CURRENT CONSUMPTION	RF transceiver in sleep mode, memory not retained				
Cortex in SHUTDOWN mode	Wake up timer running from external 32 kHz crystal, 8 kB of SRAM retained (8 kB non-retained)		680		nA
Cortex in HIBERNATE mode	(o kb hon-retained)				
RF transceiver in sleep mode,			1.6		μA
memory retained					
RF transceiver in sleep mode, memory not retained			1.38		μA
RF transceiver in receive mode			12.8		mA
RF transceiver in transmit mode			9 to 32		mA
Cortex in ACTIVE mode	RE transcoiver idle (RHV, ON or		91032		IIIA
Cortex in ACTIVE mode	RF transceiver idle (PHY_ON or PHY_OFF)				
Static current			1.8		mA
Dynamic current			190		µA/MHz
STARTUP TIME <sup>1</sup>	From applying power/asserting active external interrupt to user code execution				
From Power On and SHUTDOWN mode	FCLK is the Cortex-M3 clock or divided version of the 16 MHz oscillator.	50			ms
From FLEXI mode	From wake up event to user code execution	3 to 5			FCLK
From HIBERNATE mode Includes 310 µs for 26 MHz cry up (7 pF load capacitor at T <sub>A</sub> =			12.5		μs
RF link waking up from sleep mode			562.8		μs
POWER SUPPLY REQUIREMENTS					
Power Supply Voltage Range <sup>1</sup>		2.2		3.6	V
POWER SUPPLY MONITOR					
Trip Point voltage			2		v
POWER-ON-RESET		1	1.67		V
Watchdog Timer <sup>1</sup>					1
Timeout Period	Programmable	0		512	S

Parameter	Test Conditions/Comments	Min	Тур	Max	Unit
Flash/EE MEMORY <sup>1</sup>					
Endurance <sup>2</sup>		20,000			Cycles
Data Retention <sup>3</sup>	T <sub>J</sub> = 85°C	10			Years
Digital Inputs	All digital inputs, excluding LFXTAL1 and XOSC26P				
Input Current (leakage current)	$V_{INH} = IOVDD \text{ or } V_{INH} = 2.2V, \text{ pull up disabled.}$		10		nA
	$V_{INL} = 0V$ , pull up disabled.				
Input Capacitance			10		рF
Logic Inputs	All Logic inputs, including LFXTAL1, excluding XOSC26P				
VINL, Input Low Voltage				0.2 x IOVDD	V
VINH, Input High Voltage		0.7 x IOVDD			V
Logic Outputs					
VOH, Output High Voltage	$I_{source} = 1 \text{ mA}$	IOVDD – 0.4			v
VOL, Output Low Voltage	$I_{sink} = 1 \text{ mA}$			0.36	v
32.768 kHz CRYSTAL	32.768 kHz crystal, for use with timers	1			
	and/or RF transceiver wake up controller.				
Input Current (leakage current)	$V_{INH} = IOVDD \text{ or } V_{INH} = 2.2 \text{ V}$ $V_{INL} = 0 \text{ V}.$		50		nA
LFXTAL1 Input Capacitance			2		рF
LFXTAL2 Output Capacitance			2		pF
26 MHz CRYSTAL					r.
XOSC26P Input Capacitance			10		рF
XOSC26N Output Capacitance			10		pF
INTERNAL HF OSCILLATOR	Processor clock by default		16		MHz
Tolerance	FIOCESSOI CIOCK by default		±3		%
INTERNAL LF OSCILLATOR			±3 32.768		<sup>90</sup> kHz
					кпz %
		1	±20	120	70
MCU CLOCK DIVIDER <sup>1</sup>	8 programmable core clock dividers.	1		128	
EXTERNAL CLOCK INPUT1	External MCU clock range allowed				
Range		32.768		16000	kHz
RF LINK SPECIFICATIONS					
FREQUENCY RANGE		862		928	MHz
		431		464	MHz
PHASE-LOCKED LOOP					
Channel Frequency Resolution			396.7		Hz
Phase Noise (In-Band)	10 kHz offset, PA output power = 10		-88		dBc/Hz
	dBm				
DATA RATE					
2FSK		1		300	kbps
ООК	Manchester Encoding enabled	2.4		19.2	kbps
	(Manchester chip rate = $2 \times datarate$ )		100		Ι.
Data rate resolution			100		bps
DIFFERENTIAL PA					
Transmit Power <sup>4</sup>	Programmable.		-17 to 10		dBm
Transmit Power variation V's	From -40 °C to +85 °C, RF Frequency =		±1		dB
Temperature	868 MHz				
Transmit Power Flatness	From 902 MHz to 928 MHz and 863 MHz to 870 MHZ		±1		dB
SINGLE ENDED PA					
Transmit Power⁴	Programmable.		-21 to 13		dBm

Parameter	<b>Test Conditions/Comments</b>	Min	Тур	Max	Unit
Transmit Power variation V's Temperature	From -40°C to +85°C, RF Frequency = 868 MHz		±0.5		dB
Transmit Power Flatness	From 431 MHz to 464 MHz and 862 MHz to 928 MHZ		±1		dB
HARMONICS	868 MHz, unfiltered conductive, PA output power = 10 dBm				
Differential PA					
Second Harmonic			TBD		dBc
Third Harmonic			TBD		dBc
All Other Harmonics			TBD		dBc
OPTIMUM PA LOAD IMPEDANCE					
Single-Ended PA, in Transmit Mode					
$f_{RF} = 915 \text{ MHz}$			31.2+j10.4		Ω
$f_{\text{RF}} = 868 \text{ MHz}$			23.5+j9.7		Ω
$f_{\text{RF}} = 433 \text{ MHz}$			35.4+j3.4		Ω
Differential PA, in Transmit Mode	Load impedance between RFIO_1P and RFIO_1N to ensure maximum output power				
$f_{RF} = 915 \text{ MHz}$			38.7+j20.6		Ω
$f_{RF} = 868 \text{ MHz}$			42.2+j20.1		Ω
$f_{RF} = 433 \text{ MHz}$			55.6+j54.9		Ω
MODULATION					
<b>Deviation Frequency Resolution</b>			100		Hz
2FSK/GFSK INPUT SENSITIVITY, BIT ERROR RATE (BER)	At BER = $10^{-3}$				
1.0 kbps	Frequency deviation = 10 kHz, IF filter bandwidth = 100 kHz	-116			dBm
38.4 kbps	Frequency deviation = 19.2 kHz, IF filter bandwidth = 100 kHz		-107.5		dBm
300 kbps	Frequency deviation = 75 kHz, IF filter bandwidth = 300 kHz		-100.5		dBm
2FSK/GFSK INPUT SENSITIVITY, PACKET	At PER = 1%, packet length =20 bytes,				
ERROR RATE (PER)	packet mode				
1.0 kbps	Frequency deviation = 10 kHz, IF filter bandwidth = 100 kHz	-115.5			dBm
38.4 kbps	Frequency deviation = 19.2 kHz, IF filter bandwidth = 100 kHz		-106		dBm
300 kbps	Frequency deviation = 75 kHz, IF filter bandwidth = 300 kHz		-98		dBm
ADJACENT CHANNEL REJECTION					
CW Interferer	Wanted signal 3 dB above the input sensitivity level (BER = $10^{-3}$ ), CW interferer power level increased until BER = $10^{-3}$ , image calibrated				
200 kHz Channel Spacing	IF BW = 100 kHz, wanted signal: $F_{DEV}$ = 12.5 kHz, DR = 50 kbps	38			dB
300 kHz Channel Spacing	IF BW = 100 kHz, wanted signal: F <sub>DEV</sub> = 25 kHz, DR = 100 kbps	39			dB
600 kHz Channel Spacing	IF BW = 300 kHz, wanted signal: F <sub>DEV</sub> = 75 kHz, DR = 300 kbps	41			dB
Modulated Interferer	Wanted signal 3 dB above the input sensitivity level (BER = $10^{-3}$ ), modulated interferer with the same modulation as the wanted signal; interferer power level increased until BER = $10^{-3}$ , image calibrated				
200 kHz Channel Spacing	IF BW = 100 kHz, wanted signal: $F_{DEV} =$		38		dB

Parameter	Test Conditions/Comments	Min	Тур	Max	Unit
	12.5 kHz, DR = 50 kbps		24		10
300 kHz Channel Spacing	IF BW = 100 kHz, wanted signal: $F_{DEV}$ = 25 kHz, DR = 100 kbps		36		dB
600 kHz Channel Spacing	IF BW = 300 kHz, wanted signal: F <sub>DEV</sub> = 75 kHz, DR = 300 kbps		35		dB
CO-CHANNEL REJECTION	Desired signal 10 dB above the input sensitivity level (BER = $10^{-3}$ ), data rate = 38.4 kbps, frequency deviation = 20 kHz.		-4		dB
BLOCKING, ETSI EN 300 220	Measurement procedure as per ETSI EN 300 220-1 V2.3.1; desired signal 3 dB above the ETSI EN 300 220 reference sensitivity level of –99 dBm, IF bandwidth =100 kHz, data rate = 38.4 kbps, unmodulated interferer.				
±2 MHz			-28		dBm
±10 MHz			-20.5		dBm
WIDEBAND INTERFERENCE REJECTION	Swept from 10 MHz to 100 MHz either side of the RF frequency		75		dB
IMAGE CHANNEL ATTENUATION	Measured as image attenuation at the IF filter output, carrier wave interferer at 400 kHz below the channel frequency, 100 kHz IF filter bandwidth				
868 MHz	Uncalibrated <sup>5</sup> /calibrated		36/45		dB
RSSI					
Range at Input			−97 to −26		dBm
Linearity			±2		dB
Absolute Accuracy			±3		dB
LNA INPUT IMPEDANCE					
Receive Mode					
$f_{RF} = 915 \text{ MHz}$			68.9-j36.1		Ω
$f_{RF} = 868 \text{ MHz}$			71.6-j36.4		Ω
$f_{RF} = 433 \text{ MHz}$			99.2-j31.3		Ω
Transmit Mode					
$f_{RF} = 915 \text{ MHz}$			8.6+j21.1		Ω
$f_{RF} = 868 \text{ MHz}$			8.6+j20.4		Ω
$f_{RF} = 433 \text{ MHz}$			8.2+j11.4		Ω
RX SPURIOUS EMISSIONS					
Maximum <1 GHz	At antenna input, unfiltered conductive		TBD		dBm
Maximum >1 GHz	At antenna input, unfiltered conductive		TBD		dBm

<sup>1</sup> These numbers are not production tested, but are guaranteed by design and/or characterization data at production release.
<sup>2</sup> Endurance is gualified to 20,000 cycles as per JEDEC Std. 22 Method A117 and measured at -40°C, +25°C, and +85°C. Typical endurance at 25°C is 170,000 cycles.
<sup>3</sup> Retention lifetime equivalent at a junction temperature (T<sub>i</sub>) of 85°C as per JEDEC Std. 22 Method A117. Retention lifetime derates with junction temperature.
<sup>4</sup> Measured as the maximum unmodulated power.
<sup>5</sup> Measured with IMAGE\_REJECT\_CAL\_AMPLITUDE = 0x7 and IMAGE\_REJECT\_CAL\_PHASE = 0x16.

## **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25^{\circ}C$  unless otherwise noted

### Table 4.

Parameter	Rating
AVDD, IOVDD, VDDBAT1 and VDDBAT2 to GND	–0.3 V to 3.96 V
Digital Input Voltage to GND	–0.3 V to 3.96 V
Digital Output Voltage to GND	–0.3 V to 3.96 V
V <sub>REF</sub> to GROUND	–0.3 V to 3.96 V
Analog Inputs to GND	–0.3 V to 2.1 V
Operating Temperature Range	-40°C to +85°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	105°C
$ heta_{JA}$ Thermal Impedance	
64-Pin LFCSP _VQ	25°C/W
ESD (Human Body Model)	±1.5 kV
Peak Solder Reflow Temperature	
Pb-Free Assemblies (30 s)	260°C

### ESD CAUTION



**ESD** (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

The exposed paddle of the LFCSP package should be connected to ground.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **PIN CONFIGURATION AND FUNCTION DESCRIPTIONS**

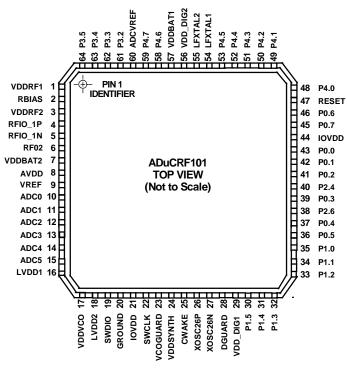


Figure 8. 64-Lead LFCSP\_VQ Pin Configuration

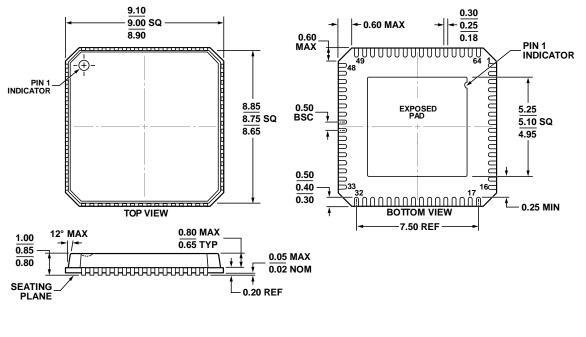
Pin	Mnemonic	Description
No.		
1	VDDRF1	Voltage Regulator output for RF block. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.
2	RBIAS	External bias resistor. A 36 k $\Omega$ resistor with 2% tolerance should be used.
3	VDDRF2	Voltage Regulator output for RF block. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.
4	RFIO_1P	LNA Positive Input in Receive Mode. Differential PA Positive Output in Transmit Mode.
5	RFIO_1N	LNA Negative Input in Receive Mode. Differential PA Negative Output in Transmit Mode.
6	RF02	Single ended PA output.
7	VDDBAT2 <sup>6</sup>	Battery Terminal, supply for the LDOs used in the RF section of the transceiver.
8	AVDD <sup>6</sup>	Battery terminal, Supply for analog circuits such as ADC and ADC internal reference, POR, PSM and LDOs.
9	VREF	Internal 1.25 V ADC reference. A 0.47 $\mu$ F capacitor between this pin and ground is required.
10	ADC0	ADC input channel 0. Input of DIFF0 pair in differential mode.
11	ADC1	ADC input channel 1. Input of DIFF0 pair in differential mode.
12	ADC2	ADC input channel 2. Input of DIFF1 pair in differential mode.
13	ADC3	ADC input channel 3. Input of DIFF1 pair in differential mode.
14	ADC4	ADC input channel 4. Input of DIFF2 pair in differential mode.
15	ADC5	ADC input channel 5. Input of DIFF2 pair in differential mode.
16	LVDD1	On chip LDO decoupling output. Connect a 0.47 $\mu$ F capacitor to the 1.8V output to ensure core operating voltage is stable. For correct operation a 1 $\mu$ F capacitor needs to be connected between this pin and LVDD2 (pin 18).
17	VDDVCO	Voltage Regulator output for VCO. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.
18	LVDD2	On chip LDO decoupling output. Connect a 0.47 $\mu$ F capacitor to the 1.32V output to ensure core operating voltage is stable. For correct operation a 1 $\mu$ F capacitor needs to be connected between this pin and LVDD1 (pin 16).
19	SWDIO	Serial Wire bi-directional data

Pin No.	Mnemonic	Description			
20	GND	Ground pin, should be connected to the PADDLE.			
21	IOVDD <sup>6</sup>	Battery terminal, General Purpose IO supply.			
22	SWCLK	Serial Wire debug clock			
23	VCOGUARD	Guard, screen for VCO, should be connected to VDDVCO.			
24	VDDSYNTH	Voltage Regulator output for Synthesizer. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.			
25	CWAKE	External capacitor for wake up control. A 150 nF capacitor should be placed between this pin and ground.			
26	XOSC26P	The 26MHz reference crystal should be connected between this pin and XOSC26N. (HFXTAL)			
27	XOSC26N	The 26MHz reference crystal should be connected between this pin and XOSC26P. (HFXTAL)			
28	DGUARD	Internal Guard, Screen for Digital Cells, should be connected to VDD_DIG1.			
29	VDD_DIG 1	Voltage Regulator output for Digital. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.			
30	P1.5/IRQ6/I2CSD A/PWM7	General Purpose Input and Output Port 1.5/External Interrupt 6/I2C Serial Data/PWM channel 7.			
31	P1.4/IRQ5/I2CSC L/PWM6	General Purpose Input and Output Port 1.4/External Interrupt 5/I2C Serial Clock/PWM channel 6.			
32	P1.3/PWM5	General Purpose Input and Output Port 1.3/PWM channel 5.			
33	P1.2/PWM4	General Purpose Input and Output Port 1.2/PWM channel 4.			
34	P1.1/PORB/TXD /PWM3	General Purpose Input and Output Port 1.1/POR output/ UART TXD/ PWM channel 3.			
35	P1.0/RXD/IRQ4/ MOSI /PWM2	General Purpose Input and Output Port 1.0/UART RXD/ External Interrupt 4/ SPI1 Master Out Slave In Pin (MOSI)/PWM channel 2.			
36	P0.5/CS2 /ECLKIN	General Purpose Input and Output Port 0.5/SPI1 Chip Select 2/External Clock Input			
37	P0.4/CS1 /ECLKOUT	General Purpose Input and Output Port 0.4/SPI1 Chip Select 1/External Clock Output.			
38	P2.6	General Purpose Input and Output Port 2.6. This pin should not be connected. This pin is connected internally to the RF transceiver. It can be used for BER measurements.			
39	P0.3/IRQ1/CS0 /ADCCONVST/P WM1	General Purpose Input and Output Port 0.3/External Interrupt 1/SPI1 Chip Select 0/ADC convert start/PWM channel 1.			
40	P2.4/IRQ8	General Purpose Input and Output Port 2.4. This pin should not be connected. This pin is connected internally to the RF transceiver. It can be used for debug purposes to monitor RF transceiver interrupt/ External Interrupt 8			
41	P0.2/MOSI/ PWM0	General Purpose Input and Output Port 0.2/SPI1 Master Out Slave In Pin (MOSI)/PWM channel 0.			
42	P0.1/SCLK	General Purpose Input and Output Port 0.1/SPI1 Serial Clock			
43	P0.0/MISO	General Purpose Input and Output Port 0.0/SPI1 Master In Slave Out Pin (MISO)			
44	IOVDD	General Purpose I/O supply. Connect to the battery terminal			
45	P0.7/IRQ3/CS4 /CTS	General Purpose Input and Output Port 0.7/ External Interrupt 3 / SPI1 Chip Select 4/ UART hand shake.			
46	BM/P <u>0.6/</u> IRQ2/CS3 / RTS/PWM0	BM (Boot Mode). The ADuCRF101 enters serial download mode if P0.6 is low during an external Reset event. It executes user code after any reset event or if P0.6 is high during an external Reset event. / General Purpose Input and Output Port 0.6/External Interrupt 2/ SPI1 Chip Select 3 / UART hand shake/PWM channel 0.			
47	RESET	Active Low. A low signal on this pin for 24 system clocks will cause the part to reset.			
48	P4.0/PWM0	General Purpose Input and Output Port 4.0/PWM channel 0.			
49	P4.1/PWM1	General Purpose Input and Output Port 4.1/PWM channel 1.			
50	P4.2/PWM2	General Purpose Input and Output Port 4.2/PWM channel 2.			
51	P4.3/PWM3	General Purpose Input and Output Port 4.3/PWM channel 3.			
52	P4.4/PWM4	General Purpose Input and Output Port 4.4/PWM channel 4.			
53	P4.5/PWM5	General Purpose Input and Output Port 4.5/PWM channel 5.			
54	LFXTAL1	32.768 kHz watch crystal output for WU timers.			
55	LFXTAL2	32.768 kHz watch crystal input for WU timers.			
56	VDD_DIG2	Voltage Regulator output for Digital section of the transceiver. A 220 nF capacitor should be placed between this pin and ground for regulator stability and noise rejection.			
57	VDDBAT16	Battery Terminal, supply for the digital section of the transceiver and GPIOs.			
58	P4.6/PWM6	General Purpose Input and Output Port 4.6/PWM channel 6.			
59	P4.7/PWM7	General Purpose Input and Output Port 4.7/PWM channel 7.			

Pin No.	Mnemonic	Description	
60	ADCVREF	Transceiver's ADC Reference Output. A 220 nF capacitor should be placed between this pin and ground for adequate noise rejection.	
61	P3.2/PWMSYNC	General Purpose Input and Output Port 3.2/PWM synchronisation.	
62	P3.3/PWMTRIP	General Purpose Input and Output Port 3.3/PWM safety cut off.	
63	P3.4	General Purpose Input and Output Port 3.4.	
64	P3.5	General Purpose Input and Output Port 3.5.	
65	PADDLE	DLE The exposed package paddle should be soldered to a metal pad on the PCB, and connected to ground.	

<sup>6</sup> VDDBAT1, VDDBAT2, AVDD and IOVDD should all be connected together.

## **OUTLINE DIMENSIONS**



#### COMPLIANT TO JEDEC STANDARDS MO-220-VMMD-4

Figure 2. 64-Lead Frame Chip Scale Package [LFCSP\_VQ] 9 mm x 9 mm Body, Very Thin Quad (CP-64-5) Dimensions shown in millimeters

#### **ORDERING GUIDE**

Model	Temperature Range	Description	Package Option
ADUCRF101BCPZ64	-40°C to 85°C	12-bit ADC, 164k Byte Flash and 8k Byte SRAM	64-lead LFCSP
ADUCRF101BCPZ128	-40°C to 85°C	12-bit ADC, 128k Byte Flash and 16k Byte SRAM	64-lead LFCSP
ADUCRF101CCPZ128	-40°C to 85°C	14-bit ADC, 128k Byte Flash and 16k Byte SRAM	64-lead LFCSP
EV-ADuCRF101MK3Z	-40°C to 85°C	Evaluation board for 433 MHz operation	N/A
EV-ADuCRF101MK1Z	-40°C to 85°C	Evaluation board for 915 MHz operation	N/A
EV- ADuCRF101QSP1Z	-40°C to 85°C	Quick start Plus for 915 MHz operation	N/A
EV-ADuCRF101QSP3Z	-40°C to 85°C	Quick start Plus for 433 MHz operation	N/A

I<sup>2</sup>C refers to a communications protocol originally developed by Philips Semiconductors (now NXP Semiconductors).

©2012 Analog Devices, Inc. All rights reserved. Trademarks and registered trademarks are the property of their respective owners. PR09464-0-11/12(PrG).



www.analog.com

06-14-2012-A

Rev. PrG | Page 13 of 13